

Dimensions

Size: 26 x 13 mils

Thickness: 5 mils

Bond Pad Size: 5 x 8 mils

Features

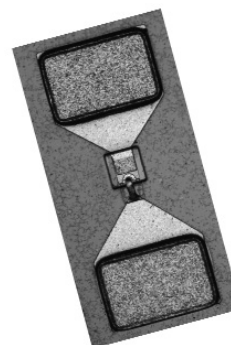
- Capacitance (45 fF Typ.)
- Low Series Resistance (7 Ω Typ.)
- Cut-off Frequency > 500 GHz
- Large Gold Bond Pads

Specifications @ 25°C (Per Junction)

- V_F (1 mA): 600–800 mV
- R_S (10 mA): 9 Ω Max.
- I_R (3 V): 10 μ A Max.
- C_T (0 V): 60 fF Max.

Maximum Ratings

Insertion Temperature	250°C for 10 Seconds
Incident Power	+20 dBm @ 25°C
Forward Current	15 mA @ 25°C
Reverse Voltage	3 V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C



Description

The MS8151-P2613 is a GaAs flip chip Schottky diode designed for use as mixer and detector elements at microwave and millimeter wave frequencies. Their high cut-off frequency insures good performance at frequencies to 100 GHz. Applications include, transceivers, digital radios and automotive radar detectors.

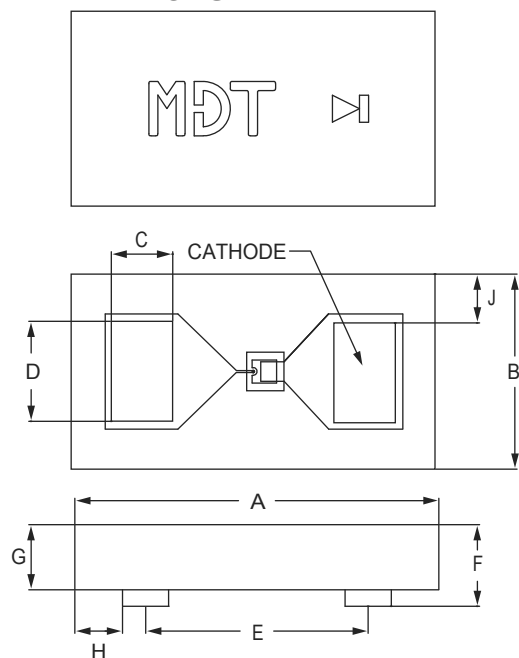
These flip chip devices incorporate Microsemi's expertise in GaAs material processing, silicon nitride protective coatings and high temperature metalization. They have large, 5 x 8 mil, bond pads for ease of insertion. The MS8150-P2613 is priced for high volume commercial and industrial applications.

IMPORTANT: For the most current data, consult our website: www.MICROSEMI.com
Specifications are subject to change. Consult factory for the latest information.



These devices are ESD sensitive and must be handled using ESD precautions.

¹ The MS8151 is supplied with a RoHS complaint Gold finish.

P2613


DIM	INCHES		MM	
	MIN.	MAX.	MIN.	MAX.
A	0.0255	0.0265	0.6480	0.6730
B	0.0125	0.0135	0.3180	0.3430
C	0.0046	0.0056	0.1170	0.1420
D	0.0075	0.0085	0.1910	0.2160
E	0.0170	0.0180	0.4320	0.4570
F	0.0050	0.0060	0.1270	0.1520
G	0.0045	0.0055	0.1140	0.1400
H	0.0016	0.0020	0.0406	0.0508
J	0.0023	0.0027	0.0584	0.0686

Spice Model Parameters (Per Junction)

I_S	R_S	N	TT	C_{J0}	C_P	M	EG	V_J	BV	IBV
A	Ω		Sec	pF	pF		eV	V	V	A
3.2×10^{-13}	7	1	0	0.025	0.02	0.50	1.42	0.85	4	1×10^{-5}